

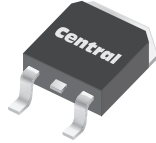
CJD31C NPN  
CJD32C PNP

**SURFACE MOUNT SILICON  
COMPLEMENTARY  
POWER TRANSISTORS**



[www.centrasemi.com](http://www.centrasemi.com)

**DPAK**  
**POWER!**



**DPAK CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CJD31C and CJD32C are complementary silicon power transistors manufactured by the epitaxial base process, mounted in a surface mount package, and designed for power amplifier and high speed switching applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

|  | SYMBOL         |             | UNITS                     |
|--|----------------|-------------|---------------------------|
| Collector-Base Voltage                       | $V_{CBO}$      | 100         | V                         |
| Collector-Emitter Voltage                    | $V_{CEO}$      | 100         | V                         |
| Emitter-Base Voltage                         | $V_{EBO}$      | 5.0         | V                         |
| Continuous Collector Current                 | $I_C$          | 3.0         | A                         |
| Peak Collector Current                       | $I_{CM}$       | 5.0         | A                         |
| Continuous Base Current                      | $I_B$          | 1.0         | A                         |
| Power Dissipation                            | $P_D$          | 15          | W                         |
| Power Dissipation ( $T_A=25^\circ\text{C}$ ) | $P_D$          | 1.56        | W                         |
| Operating and Storage Junction Temperature   | $T_J, T_{stg}$ | -65 to +150 | $^\circ\text{C}$          |
| Thermal Resistance                           | $\theta_{JC}$  | 8.33        | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance                           | $\theta_{JA}$  | 80.1        | $^\circ\text{C}/\text{W}$ |

**ELECTRICAL CHARACTERISTICS:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

| SYMBOL        | TEST CONDITIONS  | MIN | MAX | UNITS         |
|---------------|--|-----|-----|---------------|
| $I_{CEO}$     | $V_{CE}=60\text{V}$                                    |     | 50  | $\mu\text{A}$ |
| $I_{CES}$     | $V_{CE}=100\text{V}$                                   |     | 20  | $\mu\text{A}$ |
| $I_{EBO}$     | $V_{EB}=5.0\text{V}$                                   |     | 1.0 | mA            |
| $BV_{CEO}$    | $I_C=30\text{mA}$                                      | 100 |     | V             |
| $V_{CE(SAT)}$ | $I_C=3.0\text{A}, I_B=375\text{mA}$                    |     | 1.2 | V             |
| $V_{BE(ON)}$  | $V_{CE}=4.0\text{V}, I_C=3.0\text{A}$                  |     | 1.8 | V             |
| $h_{FE}$      | $V_{CE}=4.0\text{V}, I_C=1.0\text{A}$                  | 25  |     |               |
| $h_{FE}$      | $V_{CE}=4.0\text{V}, I_C=3.0\text{A}$                  | 10  | 50  |               |
| $f_T$         | $V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{MHz}$ | 3.0 |     | MHz           |
| $h_{fe}$      | $V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{kHz}$ | 20  |     |               |

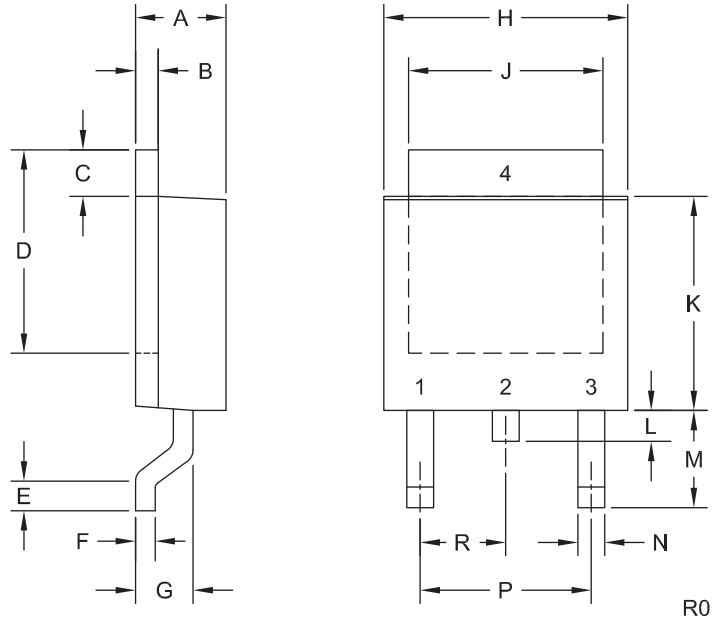
R3 (21-January 2013)

CJD31C NPN  
CJD32C PNP



**SURFACE MOUNT SILICON  
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**DPAK CASE - MECHANICAL OUTLINE**



**LEAD CODE:**

- 1) Base
- 2) Collector
- 3) Emitter
- 4) Collector

**MARKING:**

**FULL PART NUMBER**

| SYMBOL | DIMENSIONS |       |             |      |
|--------|------------|-------|-------------|------|
|        | INCHES     |       | MILLIMETERS |      |
|        | MIN        | MAX   | MIN         | MAX  |
| A      | 0.083      | 0.108 | 2.10        | 2.75 |
| B      | 0.016      | 0.032 | 0.40        | 0.81 |
| C      | 0.035      | 0.063 | 0.89        | 1.60 |
| D      | 0.203      | 0.228 | 5.15        | 5.79 |
| E      | 0.020      | -     | 0.51        | -    |
| F      | 0.018      | 0.024 | 0.45        | 0.60 |
| G      | 0.051      | 0.071 | 1.30        | 1.80 |
| H      | 0.248      | 0.268 | 6.30        | 6.81 |
| J      | 0.197      | 0.217 | 5.00        | 5.50 |
| K      | 0.209      | 0.245 | 5.30        | 6.22 |
| L      | 0.025      | 0.040 | 0.64        | 1.02 |
| M      | 0.090      | 0.115 | 2.30        | 2.91 |
| N      | 0.012      | 0.045 | 0.30        | 1.14 |
| P      | 0.180      |       | 4.60        |      |
| R      | 0.090      |       | 2.30        |      |

DPAK (REV: R0)

R3 (21-January 2013)

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### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

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### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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